Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt[®] G5



www.vishay.com

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS						
I _{F(AV)} 30 A						
V _R	1200 V					
V _F at I _F at 125 °C	2.1 V					
t _{rr}	26 ns					
T _J max.	175 °C					
Package	2L TO-220AC					
Circuit configuration	Single					

FEATURES

- Hyperfast and optimized Q_{rr}
- Best in class forward voltage drop and switching RoHS
 losses trade off
 HALOGEN
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MECHANICAL DATA

Case: 2L TO-220AC

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002 and JESD 22-B102

Polarity: as per marking device details

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Repetitive peak reverse voltage	V _{RRM}		1200	V			
Average rectified forward current	I _{F(AV)}	T _C = 83 °C, D = 0.50	30				
Non-repetitive peak surge current	I _{FSM}	T_{C} = 83 °C, t_{p} = 10 ms, sine wave	190	A			
Repetitive peak forward current	I _{FRM}	T _C = 45 °C, D = 0.50, f = 20 kHz	60				
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)								
PARAMETER	SYMBOL	BOL TEST CONDITIONS MIN.		TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	1200	-	-			
Forward voltage	V _F	I _F = 30 A	-	2.6	3.3	V		
		I _F = 30 A, T _J = 125 °C	-	2.1	-			
	I _R	$V_{R} = V_{R}$ rated	-	-	50			
Reverse leakage current		$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA		
Junction capacitance	CT	V _R = 200 V	-	17	-	pF		
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH		

 Revision: 30-Jul-2020
 1
 Document Number: 96612

 For technical questions within your region: DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com
 DiodesEurope@vishay.com

 THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



FREE



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
		I _F = 1.0 A, dI _F /dt =	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 100 \text{ A}/\mu\text{s}, V_R = 30 \text{ V}$		26	47		
Reverse recovery time	t _{rr}	T _J = 25 °C		-	100	-	ns	
		T _J = 125 °C		-	150	-		
Peak recovery current		T _J = 25 °C	I _F = 20 A dI _F /dt = 600 A/μs V _R = 400 V	-	12	-	A	
	I _{RRM}	T _J = 125 °C		-	22	-		
Powerse receivery charge	0	T _J = 25 °C		-	530	-	nC	
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1650	-		
Reverse recovery time	+	T _J = 25 °C		-	80	-	ns	
neverse recovery time	t _{rr}	T _J = 125 °C		-	120	-	115	
Poole recovery ourrent		T _J = 25 °C	I _F = 30 A dI _F /dt = 1000 A/μs V _R = 800 V	-	22	-	A	
Peak recovery current	I _{RRM}	T _J = 125 °C		-	37	-		
Reverse recovery charge	0	T _J = 25 °C		-	900	-		
	Q _{rr}	T _J = 125 °C]	-	2400	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.1	°C/W	
147.1.1.1			-	2.0	-	g	
Weight			-	0.07	-	oz.	
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)	
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C	
Marking device		Case style: 2L TO-220AC	E5TX3012				

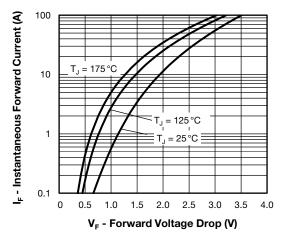


Fig. 1 - Typical Forward Voltage Drop Characteristics

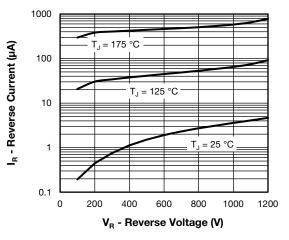


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

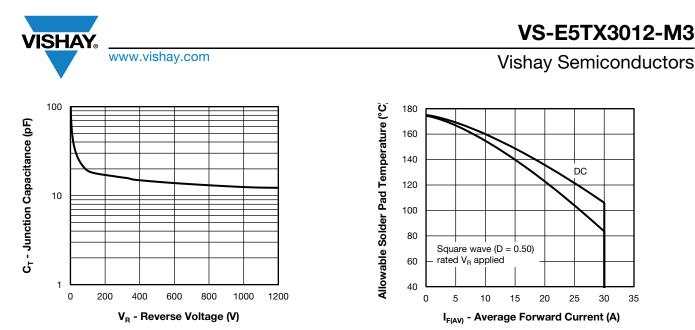


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

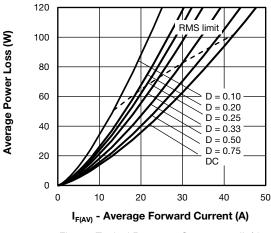


Fig. 5 - Typical Recovery Current vs. dl_F/dt

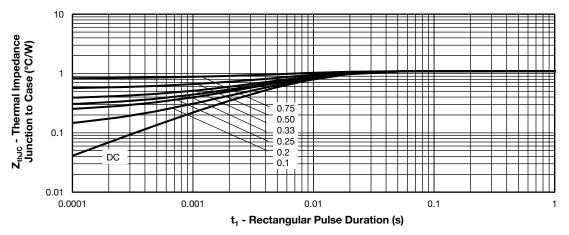


Fig. 6 - Thermal Impedance Z_{thJC} Characteristics

Revision: 30-Jul-2020 For technical questions within your region:



VS-E5TX3012-M3

Vishay Semiconductors

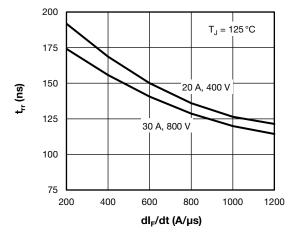


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

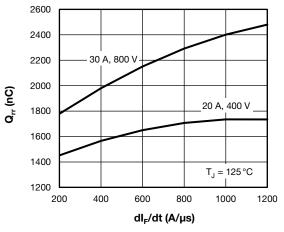


Fig. 8 - Typical Stored Charge vs. dl_F/dt

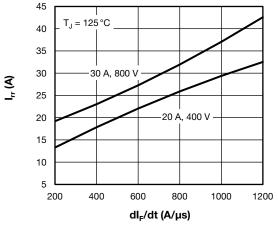


Fig. 9 - Typical Recovery Current vs. dl_F/dt



Vishay Semiconductors

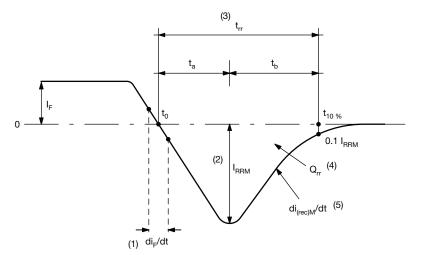


Fig. 10 - Reverse Recovery Waveform and Definitions

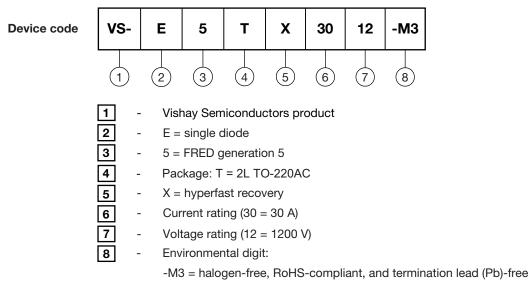
Notes

- (1) di_F/dt rate of change of current through zero crossing
- ⁽²⁾ I_{RRM} peak reverse recovery current
- $^{(3)}$ t_{rr} reverse recovery time measured from t₀, crossing point of negative going I_F, to point t_{10%}, 0.1 I_{RRM}
- $^{(4)}~~\text{Q}_{rr}$ area under curve defined by t_0 and $t_{10~\%}$

$$Q_{rr} = \int\limits_{t_0}^{t_{10}\,\%} I(t)dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)							
PREFERRED P/N	RED P/N QUANTITY PER TUBE MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-E5TX3012-M3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96154
Part marking information	www.vishay.com/doc?95391

Revision: 30-Jul-2020

Document Number: 96612

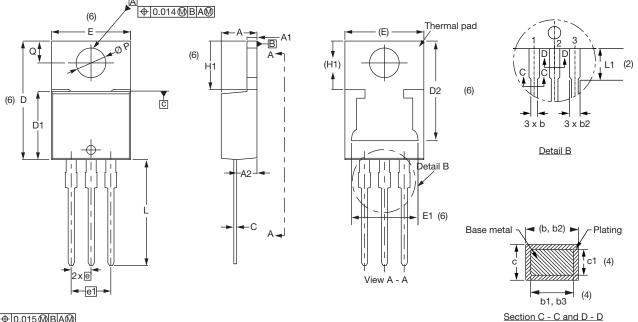
For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



Vishay Semiconductors

3L TO-220AB

DIMENSIONS in millimeters and inches



⊕0.015@BA@





SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

_		
Conforms to JEDEC [®]	outline	TO-220AB

SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STINDOL	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
Ш	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

⁽²⁾ Lead dimension and finish uncontrolled in L1

- ⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only
- (5) Controlling dimensions: inches
- ⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1
- ⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

Revision: 13-Jun-2019

 $^{^{(1)}\,}$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽³⁾ Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.